

General Description

The Alpha IGBT™ line of products offers best-in-class performance in conduction and switching losses, with robust short circuit capability. They are designed for ease of paralleling, minimal gate spike under high dV/dt conditions and resistance to oscillations. The soft co-packaged diode is targeted for minimal losses in Welding machines, Solar Inverter and UPS applications.

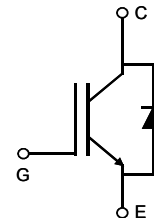
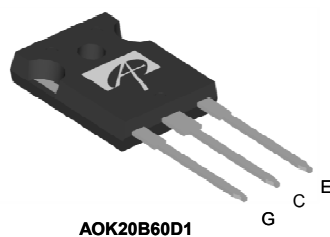
Product Summary

V_{CE}	600V
I_C ($T_C=100^\circ\text{C}$)	20A
$V_{CE(sat)}$ ($T_C=25^\circ\text{C}$)	1.85V



Top View

TO-247



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	AOK20B60D1	Units
Collector-Emitter Voltage		V_{CE}	600	V
Gate-Emitter Voltage		V_{GE}	±20	V
V_{GE} Spike	500ns	V_{SPIKE}	24	V
Continuous Collector Current	$T_C=25^{\circ}\text{C}$	I_C	40	A
	$T_C=100^{\circ}\text{C}$		20	
Pulsed Collector Current, Limited by T_{Jmax}		I_{CM}	74	A
Turn off SOA, $V_{CE} \leq 600\text{V}$, Limited by T_{Jmax}		I_{LM}	74	A
Continuous Diode Forward Current	$T_C=25^{\circ}\text{C}$	I_F	20	A
	$T_C=100^{\circ}\text{C}$		10	
Diode Pulsed Current, Limited by T_{Jmax}		I_{FM}	74	A
Short circuit withstanding time $V_{GE} = 15\text{V}$, $V_{CE} \leq 400\text{V}$, Delay between short circuits $\geq 1.0\text{s}$, $T_C=25^{\circ}\text{C}$		t_{SC}	10	μs
Power Dissipation	$T_C=25^{\circ}\text{C}$	P_D	139	W
	$T_C=100^{\circ}\text{C}$		56	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	AOK20B60D1	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	40	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.9	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV_{CES}	Collector-Emitter Breakdown Voltage	$I_C=1\text{mA}$, $V_{GE}=0\text{V}$, $T_J=25^\circ\text{C}$	600	-	-	V	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE}=15\text{V}$, $I_C=20\text{A}$	$T_J=25^\circ\text{C}$	-	1.85	2.4	V
			$T_J=125^\circ\text{C}$	-	2.2	-	
			$T_J=150^\circ\text{C}$	-	2.3	-	
V_F	Diode Forward Voltage	$V_{GE}=0\text{V}$, $I_C=10\text{A}$	$T_J=25^\circ\text{C}$	-	1.35	1.85	V
			$T_J=125^\circ\text{C}$	-	1.33	-	
			$T_J=150^\circ\text{C}$	-	1.3	-	
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$V_{CE}=5\text{V}$, $I_C=1\text{mA}$	-	5.7	-	V	
I_{CES}	Zero Gate Voltage Collector Current	$V_{CE}=600\text{V}$, $V_{GE}=0\text{V}$	$T_J=25^\circ\text{C}$	-	-	10	μA
			$T_J=125^\circ\text{C}$	-	-	300	
			$T_J=150^\circ\text{C}$	-	-	1500	
I_{GES}	Gate-Emitter leakage current	$V_{CE}=0\text{V}$, $V_{GE}=\pm 20\text{V}$	-	-	± 100	nA	
g_{FS}	Forward Transconductance	$V_{CE}=20\text{V}$, $I_C=20\text{A}$	-	7	-	S	
DYNAMIC PARAMETERS							
C_{ies}	Input Capacitance	$V_{GE}=0\text{V}$, $V_{CE}=25\text{V}$, $f=1\text{MHz}$	-	984	-	pF	
C_{oes}	Output Capacitance		-	93	-	pF	
C_{res}	Reverse Transfer Capacitance		-	3.75	-	pF	
Q_g	Total Gate Charge	$V_{GE}=15\text{V}$, $V_{CE}=480\text{V}$, $I_C=20\text{A}$	-	24.6	-	nC	
Q_{ge}	Gate to Emitter Charge		-	9.8	-	nC	
Q_{gc}	Gate to Collector Charge		-	8.2	-	nC	
$I_{C(SC)}$	Short circuit collector current, Max. 1000 short circuits, Delay between short circuits $\geq 1.0\text{s}$	$V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_G=25\Omega$	-	74	-	A	
R_g	Gate resistance	$f=1\text{MHz}$	-	2.5	-	Ω	
SWITCHING PARAMETERS, (Load Inductive, $T_J=25^\circ\text{C}$)							
$t_{D(on)}$	Turn-On DelayTime	$T_J=25^\circ\text{C}$ $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$, $R_G=15\Omega$, Parasitic Inductance=150nH	-	20	-	ns	
t_r	Turn-On Rise Time		-	37	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	66	-	ns	
t_f	Turn-Off Fall Time		-	8	-	ns	
E_{on}	Turn-On Energy		-	0.76	-	mJ	
E_{off}	Turn-Off Energy		-	0.18	-	mJ	
E_{total}	Total Switching Energy		-	0.94	-	mJ	
t_{rr}	Diode Reverse Recovery Time	$T_J=25^\circ\text{C}$ $I_F=10\text{A}$, $dI/dt=200\text{A}/\mu\text{s}$, $V_{CE}=400\text{V}$	-	107	-	ns	
Q_{rr}	Diode Reverse Recovery Charge		-	0.43	-	μC	
I_{rm}	Diode Peak Reverse Recovery Current		-	6.5	-	A	
SWITCHING PARAMETERS, (Load Inductive, $T_J=150^\circ\text{C}$)							
$t_{D(on)}$	Turn-On DelayTime	$T_J=150^\circ\text{C}$ $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$, $R_G=15\Omega$, Parasitic Inductance=150nH	-	20	-	ns	
t_r	Turn-On Rise Time		-	38	-	ns	
$t_{D(off)}$	Turn-Off Delay Time		-	81	-	ns	
t_f	Turn-Off Fall Time		-	14	-	ns	
E_{on}	Turn-On Energy		-	0.9	-	mJ	
E_{off}	Turn-Off Energy		-	0.33	-	mJ	
E_{total}	Total Switching Energy		-	1.23	-	mJ	
t_{rr}	Diode Reverse Recovery Time	$T_J=150^\circ\text{C}$ $I_F=10\text{A}$, $dI/dt=200\text{A}/\mu\text{s}$, $V_{CE}=400\text{V}$	-	180	-	ns	
Q_{rr}	Diode Reverse Recovery Charge		-	0.78	-	μC	
I_{rm}	Diode Peak Reverse Recovery Current		-	8.4	-	A	

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

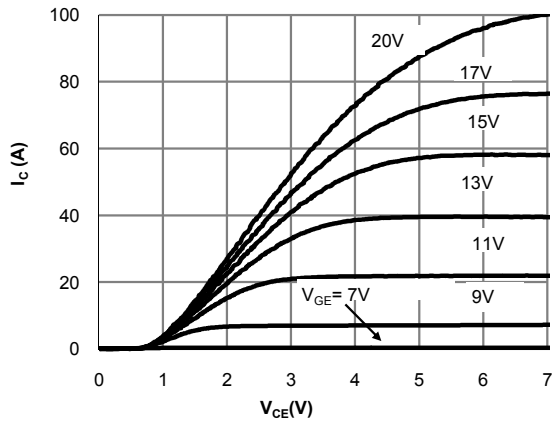


Fig 1: Output Characteristic
($T_j = 25^\circ\text{C}$)

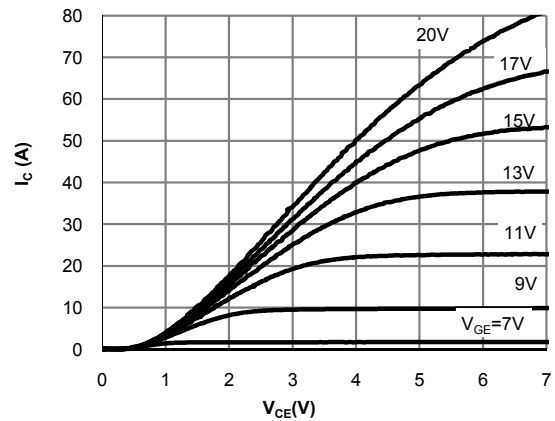


Fig 2: Output Characteristic
($T_j = 150^\circ\text{C}$)

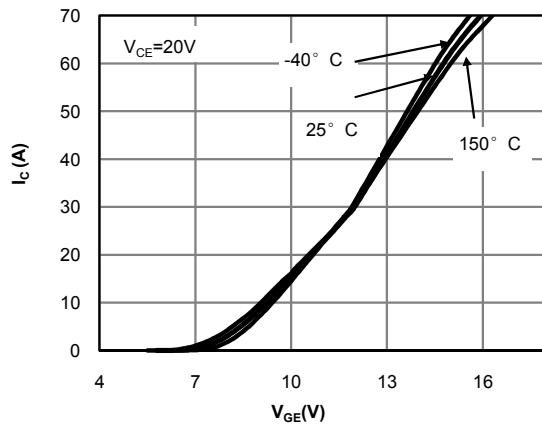


Fig 3: Transfer Characteristic

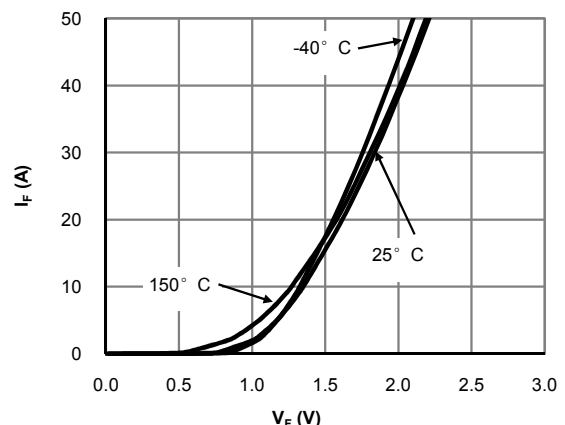


Fig 4: Diode Characteristic

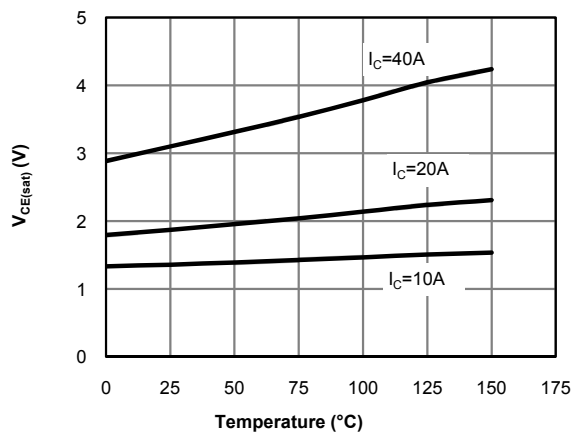


Fig 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

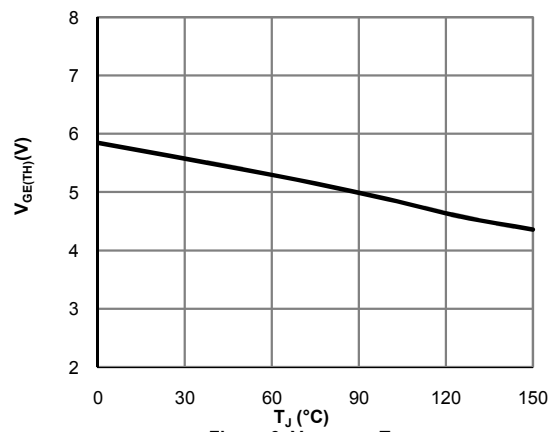
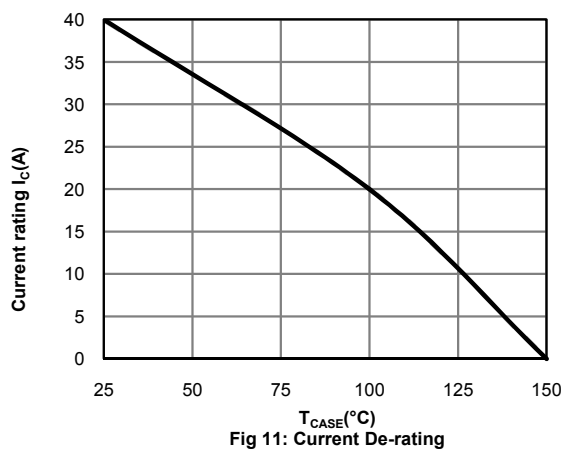
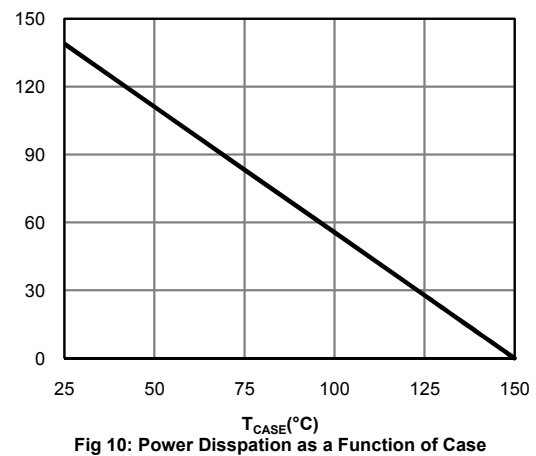
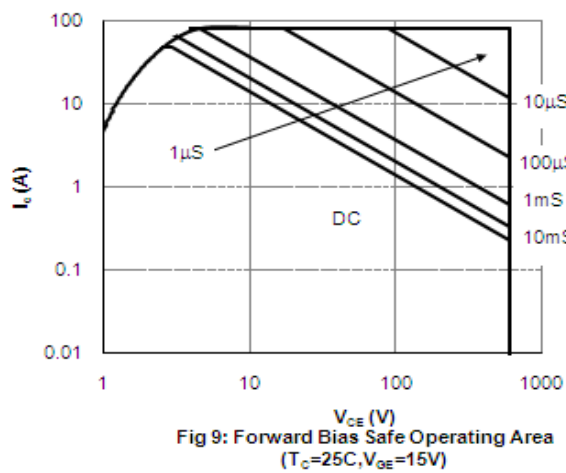
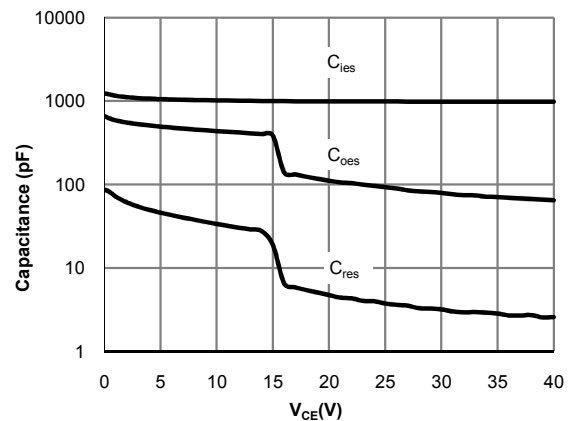
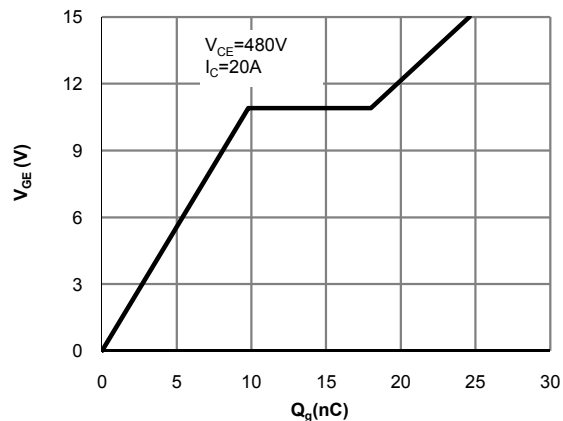


Figure 6: $V_{GE(TH)}$ vs. T_j

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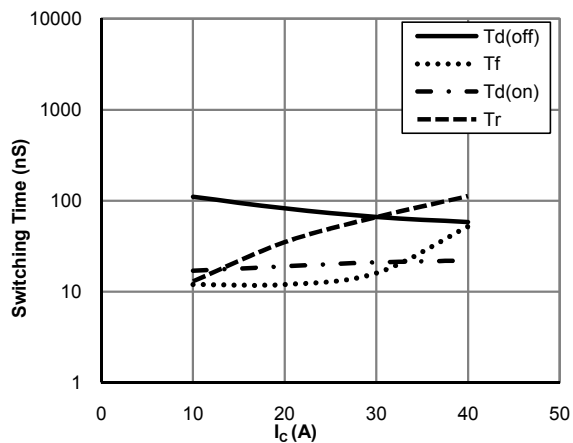


Figure 12: Switching Time vs. I_C
(T_J=150°C, V_{GE}=15V, V_{CE}=400V, R_g=15Ω)

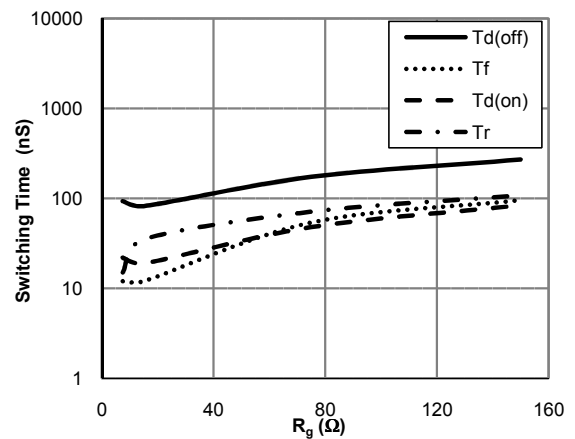


Figure 13: Switching Time vs. R_g
(T_J=150°C, V_{GE}=15V, V_{CE}=400V, I_C=20A)

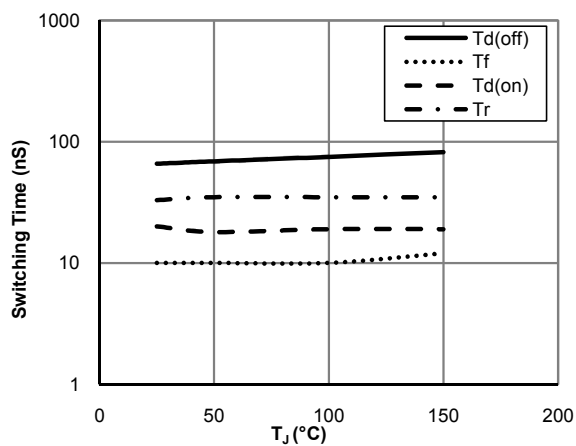


Figure 14: Switching Time vs. T_J
(V_{GE}=15V, V_{CE}=400V, I_C=20A, R_g=15Ω)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

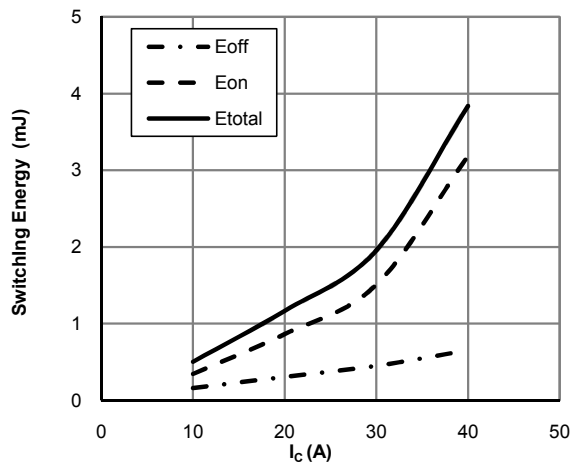


Figure 15: Switching Loss vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=15\Omega$)

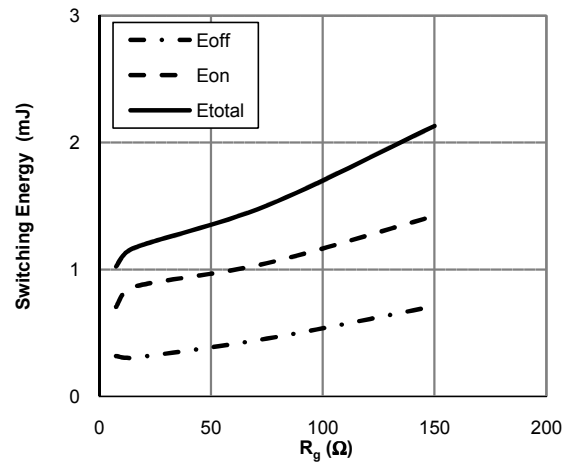


Figure 16: Switching Loss vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$)

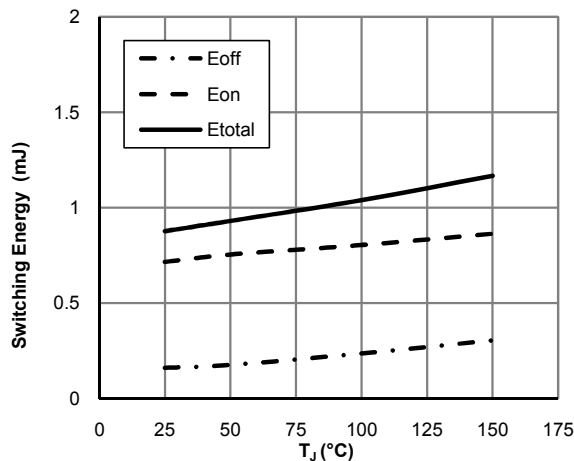


Figure 17: Switching Loss vs. T_J
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=20\text{A}$, $R_g=15\Omega$)

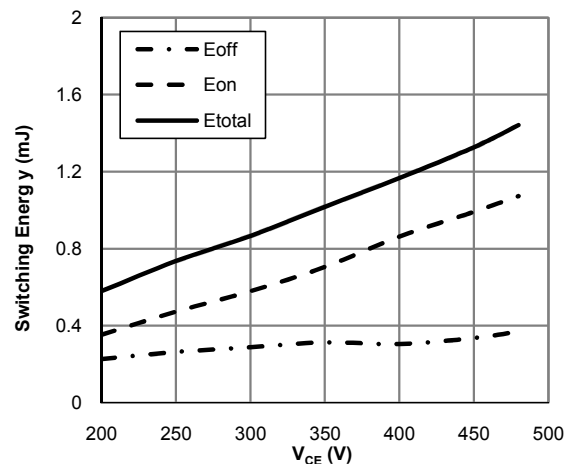


Figure 18: Switching Loss vs. V_{CE}
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $I_C=20\text{A}$, $R_g=15\Omega$)

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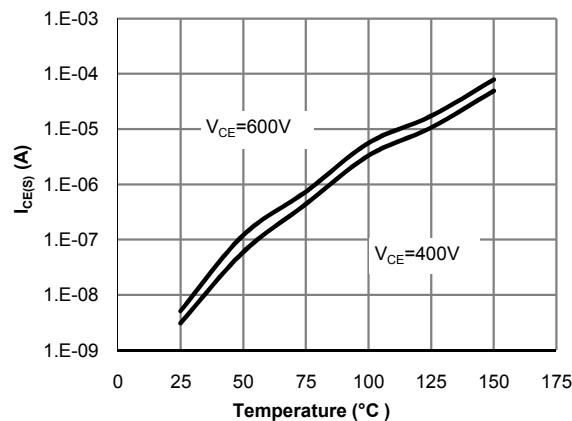


Fig 19: Diode Reverse Leakage Current vs. Junction Temperature

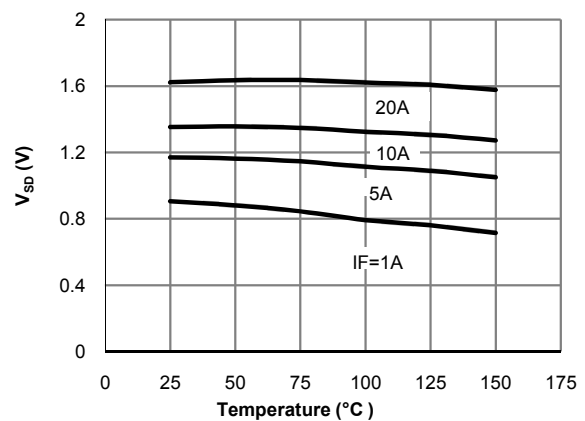


Fig 20: Diode Forward Voltage vs. Junction Temperature

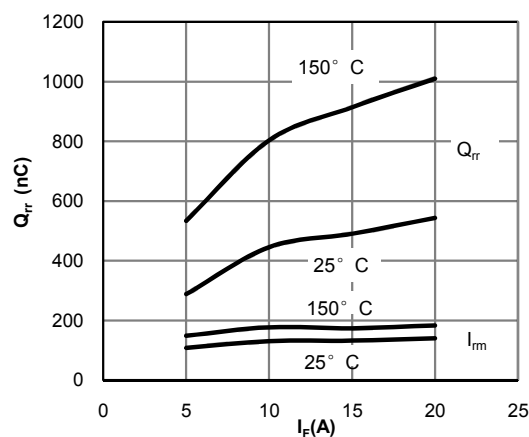


Fig 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

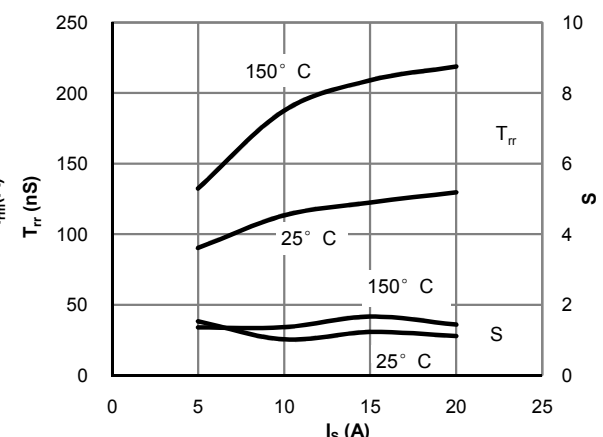


Fig 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V, V_{CE}=400V, di/dt=200A/\mu s$)

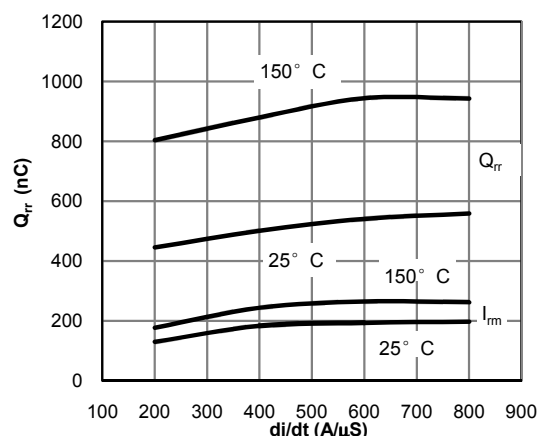


Fig 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

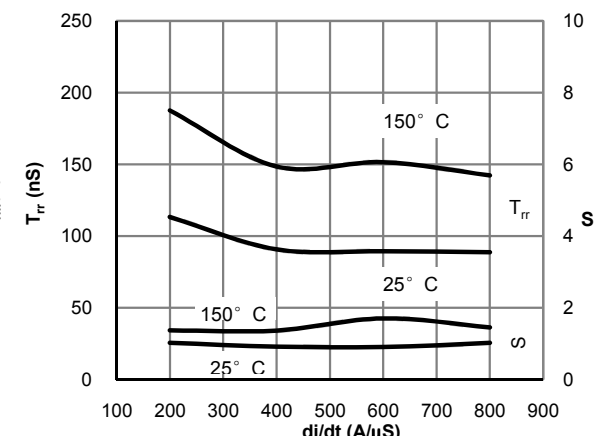


Fig 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V, V_{CE}=400V, I_F=10A$)

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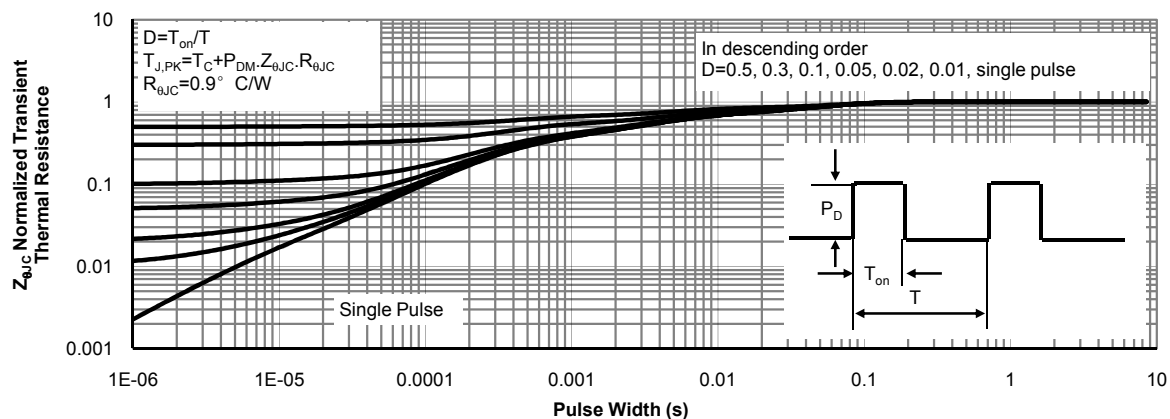


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

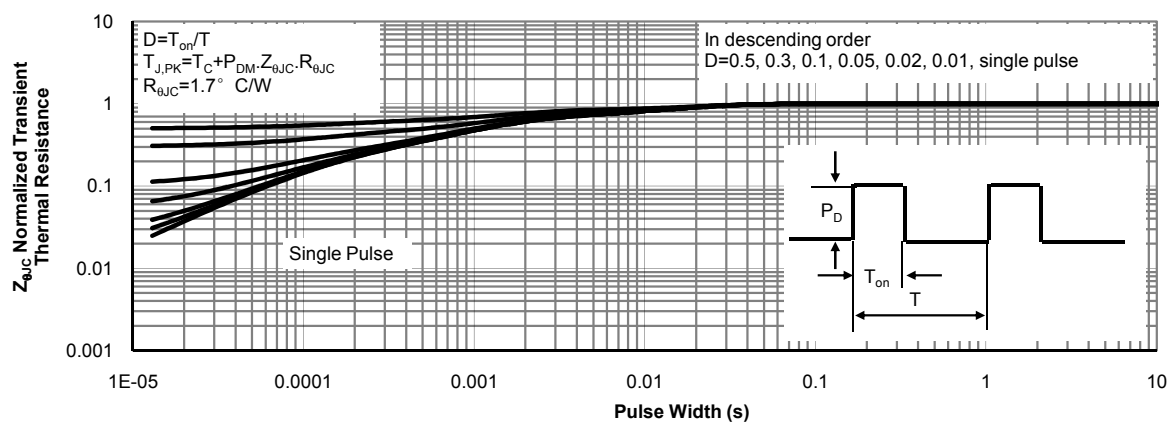
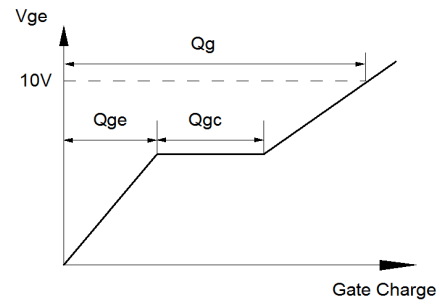
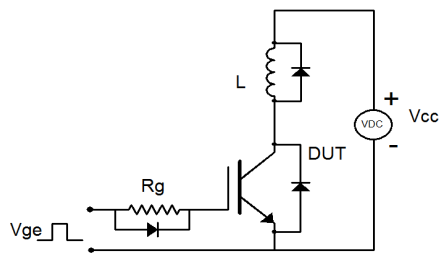
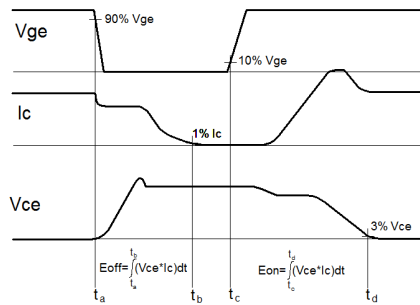
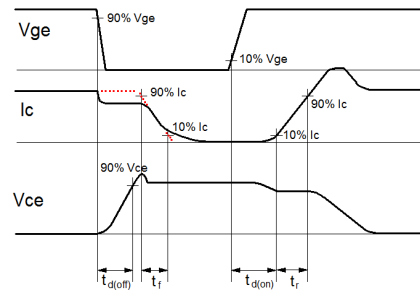
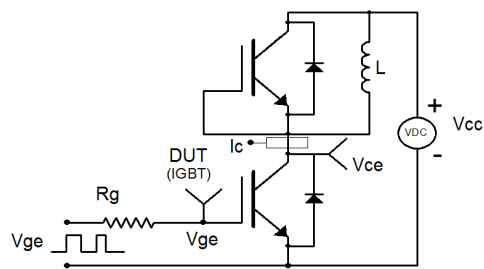


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

Gate Charge Test Circuit & Waveform



Inductive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

